

SEMICONDUCTOR DEVICE AND PROCESS OF PRODUCTION OF SAME

ABSTRACT OF THE DISCLOSURE

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A semiconductor device comprising: a first
insulating film formed on a semiconductor substrate; a
semiconductor layer at least a part of which is formed on
the first insulating film; a second insulating film
10 comprising a non-doped silicon oxide film and formed on
the semiconductor layer; a third insulating film
comprising a silicon oxide film containing at least
phosphorus formed on the second insulating film; and a
fourth insulating film comprising a non-doped silicon
15 oxide film formed on the third insulating film.